

IN THE CLAIMS:

Please amend the claims as indicated below.

1. (Currently Amended) A method of manufacturing a thin-film semiconductor device, comprising:

 ~~the~~ a step of preparing a member having a semiconductor film with a semiconductor element and/or semiconductor integrated circuit on a separation layer;

 ~~the~~ a separation step of separating the member at the separation layer by applying a pressure of a fluid to the side surface of the separation layer; and

 ~~the~~ a chip forming step of, after the separation step, ~~forming~~ dividing the semiconductor film into chips.
2. (Original) The method according to claim 1, wherein the member is obtained by forming a porous layer on a surface of a semiconductor substrate, forming the semiconductor film on a surface of the porous layer, and then forming the semiconductor element and/or semiconductor integrated circuit.
3. (Original) The method according to claim 2, wherein the semiconductor film is formed on the surface of the porous layer after forming a protective film on inner walls of pores in the porous layer.
4. (Original) The method according to claim 1, wherein the member is obtained by forming the semiconductor element and/or semiconductor integrated circuit on

a surface of a semiconductor substrate and implanting ions from the surface side to a predetermined depth to form the separation layer.

5. (Original) The method according to claim 2, wherein the semiconductor substrate is a single-crystal silicon substrate or a compound semiconductor substrate.

6. (Original) The method according to claim 4, wherein the semiconductor substrate is a single-crystal silicon substrate or a compound semiconductor substrate.

7. (Cancelled).

8. (Original) The method according to claim 1, wherein after the separation step, the separation layer remaining on the semiconductor film side is removed, and then, the chip forming step is executed.

9. (Original) The method according to claim 1, wherein after the separation step and the chip forming step, the step of removing the separation layer remaining on the semiconductor film side is executed.

10. (Currently Amended) A method of manufacturing a thin-film semiconductor device, comprising:

~~the a~~ step of preparing a member having a semiconductor film with a semiconductor element and/or semiconductor integrated circuit on a separation layer;

a bonding step of bonding the member to a support member;

~~the a~~ chip forming step of, after the bonding step, dividing forming the member into chips in desired regions; and

~~the a~~ separation step of, after the chip forming step, separating the member at the separation layer.

11. (Cancelled).

12. (Cancelled).

13. (New) A method of manufacturing a thin-film semiconductor device, comprising:

a step of preparing a member having a semiconductor film with a semiconductor element and/or semiconductor integrated circuit on a separation layer;

a bonding step of bonding the member to a support member;

a separation step of, after the bonding step, separating the member at the separation layer by a pressure of a fluid; and

a chip forming step of, after the separation step, dividing the semiconductor film into chips.